NSN 5961-01-224-3670

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-224-3670 **Inclosure Material:** Metal **Overall Length:** 1.646 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 150.0 nonrepetitive peak reverse voltage, peak total value, gate terminal open-circuited and 100.0 repetitive peak reverse voltage, peak total value, gate terminal open-circuited **Current Rating Per Characteristic:** 125.00 amperes source cutoff current absolute and 16.00 amperes source cutoff current preset **Power Rating Per Characteristic:** 50.0 watts small-signal input power, common-collector of standard range **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpnp **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:**

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